

AMENDMENT TO THE CLAIMS

Kindly cancel claims 1, 3, 4 and 10 without prejudice or admission. Kindly amend claims 2 and 5-9 as follows:

Claim 1 (Cancelled)

Claim 2 (Currently Amended): ~~The A~~ method of fabricating a thin integrated film circuit as claimed in claim 1, ~~wherein the fabrication process of integrating thick film resistor components with a thin film circuit portion on a printed circuit board involves a first phase process of forming the~~ with thick film resistors, comprising the ~~acts~~ steps of :

forming multiple pairs of conductive electrodes as terminals of (11) ~~for~~ thick film resistors on a substrate, wherein the two conductive electrodes of the same pair are separated by a distance and extend parallel to each other ~~pairs of electrodes (11) are formed at predetermined positions over a substrate (1) and each electrode pair acts as the end terminals of the thick film resistors;~~

forming a resistive coating (12) ~~for thick film resistors in~~ on the substrate between the ~~electrode pairs~~ each pair of conductive electrodes to ~~finish~~ form a thick film resistor;

forming a passivation layer (13) over the thick film resistors, where a low temperature process is used to form a dielectric layer as the passivation layer to protect the thick film resistors;

forming a titanium layer and a copper layer sequentially over the substrate with the thick film resistors;

attaching a dry film as over the copper layer;

providing a photomask over the dry film;

forming a circuit pattern on the dry film by an exposing process;

electroplating a copper plated circuit on the circuit pattern that connects to the thick film resistors;

removing remnants of the dry film and excess portions of the copper layer and titanium layer from the substrate to form thin film circuit.

Claim 3 (Cancelled)

Claim 4 (Cancelled)

Claim 5 (Currently Amended): The method ~~of fabricating a thin film circuit~~ as claimed in claim 2, wherein the ~~formation~~ forming of the conductive electrodes, ~~(11)~~ and the resistive coating ~~(12)~~ for the thick film resistors, and the passivation layer ~~(13)~~ all require a high temperature sintering or baking process after finishing the coating.

Claim 6 (Currently Amended): The method ~~of fabricating a thin film circuit~~ as claimed in claim 2 5, wherein the ~~formation~~ forming of the conductive electrodes, ~~(11)~~ and the resistive coating ~~(12)~~ for the thick film resistors, and the passivation layer ~~(13)~~ all use a screen printing technique.

Claim 7 (Currently Amended): The method ~~of fabricating a thin film circuit~~ as claimed in claim 2, wherein ~~the coating of the electrode~~ conductive electrodes layer ~~has~~ have a thickness of $25 \pm 5 \mu\text{m}$.

Claim 8 (Currently Amended): The method ~~of fabricating a thin film circuit~~ as claimed in claim 2, wherein ~~the coating of~~ the passivation layer ~~(13)~~ has a thickness of $18 \pm 3 \mu\text{m}$.

Claim 9 (Currently Amended): The method ~~of fabricating a thin film circuit~~ as claimed in claim 3 6, wherein the titanium layer ~~(21)~~ and the copper layer ~~(22)~~ are formed by a sputtering process.

Claim 10 (Cancelled)